

SINGLE AND DOUBLE GATE FIELD EFFECT TRANSISTORS WITH SIDEWALL SOURCE-DRAIN CONTACTS

ABSTRACT

The present invention concerns single-gate and double-gate (10) field effect transistors having a sidewall source contact and a sidewall drain contact, and methods for making such field effect transistors. The channel (15) of the present field effect transistors is raised with respect to the support structure underneath and the source (20.1) and drain (20.2) regions form an integral part of the channel (15).

Fig. 1